

# Table 1

Experimental conditions of channel doping  
with respect to the silicon-containing amorphous semiconductor film

substrate No.	chemical oxide film	diborane dilution ratio
1	None	0.1%B <sub>2</sub> H <sub>6</sub> /H <sub>2</sub>
2	Exist	0.1%B <sub>2</sub> H <sub>6</sub> /H <sub>2</sub>
3	None	1.0%B <sub>2</sub> H <sub>6</sub> /H <sub>2</sub>
4	Exist	1.0%B <sub>2</sub> H <sub>6</sub> /H <sub>2</sub>

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